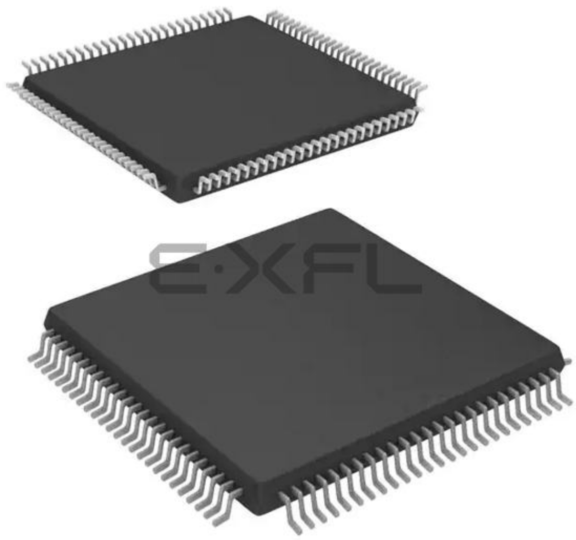

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p060-1vqg100t

Automotive ProASIC3 Ordering Information

A3P1000 – 1 FG G 144 Y T

- **Application (Temperature Range)**
  - T = Grade 2 and Grade 1 AEC-Q100
    - Grade 2 = 105°C T_A and 115°C T_J[1]
    - Grade 1 = 125°C T_A and 135°C T_J[1]
- **Security Feature**
  - Y = Device Includes License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio
  - Blank = Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio
- **Package Lead Count**
- **Lead-Free Packaging**
  - Blank = Standard Packaging
  - G = RoHS-Compliant (Green) Packaging
- **Package Type**
  - VQ = Very Thin Quad Flat Pack (0.5 mm pitch)
  - FG = Fine Pitch Ball Grid Array (1.0 mm pitch)
  - QN = Quad Flat Pack (0.5 mm pitch)
- **Speed Grade**
  - Blank = Standard
  - 1 = 15% Faster than Standard
- **Part Number**
  - **Automotive ProASIC3 Devices**
    - A3P060 = 60,000 System Gates
    - A3P125 = 125,000 System Gates
    - A3P250 = 250,000 System Gates
    - A3P1000 = 1,000,000 System Gates

Notes:

1. *T_A = Ambient temperature and T_J = Junction temperature.*
2. *Minimum order quantities apply. Contact your local Microsemi SoC Products Group sales office for details.*

Temperature Grade Offerings

Package	A3P060	A3P125	A3P250	A3P1000
VQ100	C, I, T	C, I, T	C, I, T	–
FG144	C, I, T	C, I, T	C, I, T	C, I, T
FG256	–	–	C, I, T	C, I, T
FG484	–	–	–	C, I, T
QNG132	–	C, I, T	C, I, T	–

Notes:

1. *C = Commercial temperature range: 0°C to 70°C*
2. *I = Industrial temperature range: –40°C to 85°C*
3. *T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100*
   Grade 2 = 105°C T_A and 115°C T_J
   Grade 1 = 125°C T_A and 135°C T_J
4. *Specifications for Commercial and Industrial grade devices can be found in the* ProASIC3 Flash Family FPGAs *datasheet.*

Speed Grade and Temperature Grade Matrix

Temperature Grade	Std.	–1
T (Grade 1 and Grade 2), Commercial, Industrial	3	3

Notes:

1. *T = Automotive temperature range: Grade 2 and Grade 1 AEC-Q100*
   Grade 2 = 105°C T_A and 115°C T_J
   Grade 1 = 125°C T_A and 135°C T_J
2. *Specifications for Commercial and Industrial grade devices can be found in the* ProASIC3 Flash Family FPGAs *datasheet.*

Contact your local Microsemi SoC Products Group representative for device availability:
http://www.microsemi.com/soc/contact/default.aspx.

User Nonvolatile FlashROM

Automotive ProASIC3 devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Unique protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, infotainment systems)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard Automotive ProASIC3 IEEE 1532 JTAG programming interface.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

Automotive ProASIC3 development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

SRAM

Automotive ProASIC3 devices have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro.

PLL and CCC

Automotive ProASIC3 devices provide designers with very flexible clock conditioning circuit (CCC) capabilities. Each member of the Automotive ProASIC3 family contains six CCCs. One CCC (center west side) has a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides. One CCC (center west side) has a PLL.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Table 2-10 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings [1] Applicable to Standard Plus I/O Banks**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	452.67
2.5 V LVCMOS	35	2.5	–	258.32
1.8 V LVCMOS	35	1.8	–	133.59
1.5 V LVCMOS (JESD8-11)	35	1.5	–	92.84
3.3 V PCI	10	3.3	–	184.92
3.3 V PCI-X	10	3.3	–	184.92

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VMV.*
3. *PAC10 is the total dynamic power measured on VCCI and VMV.*

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-14 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Slew Rate	VIL Min. V	VIL Max. V	VIH Min. V	VIH Max. V	VOL Max. V	VOH Min. V	I_{OL} mA	I_{OH} mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
2.5 V LVCMOS	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	High	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI	Per PCI specifications									
3.3 V PCI-X	Per PCI-X specifications									

Note: Currents are measured at 125°C junction temperature.

Table 2-15 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Standard Plus I/O Banks**

I/O Standard	Drive Strength	Slew Rate	VIL Min. V	VIL Max. V	VIH Min. V	VIH Max. V	VOL Max. V	VOH Min. V	I_{OL} mA	I_{OH} mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
2.5 V LVCMOS	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	High	–0.3	0.30 * VCCI	0.7 * V_{CCI}	3.6	0.25 * VCCI	0.75 * V_{CCI}	4	4
3.3 V PCI	Per PCI specifications									
3.3 V PCI-X	Per PCI-X specifications									

Note: Currents are measured at 125°C junction temperature.

Table 2-16 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Slew Rate	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}
			Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
2.5 V LVCMOS	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	High	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2

Note: Currents are measured at 125°C junction temperature.

Table 2-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Automotive Grade 1 and Grade 2

DC I/O Standards	Automotive Grade 1 [1]		Automotive Grade 2 [2]	
	IIL	IIH	IIL	IIH
	µA	µA	µA	µA
3.3 V LVTTL / 3.3 V LVCMOS	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15

Notes:

1. *Automotive range Grade 1 (–40°C < T_J < 135°C)*
2. *Automotive range Grade 2 (–40°C < T_J < 115°C)*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-18 • Summary of AC Measuring Points

Standard	Measuring Trip Point (Vtrip)
3.3 V LVTTL / 3.3 V LVCMOS	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
3.3 V PCI	0.285 * VCCI (RR)
	0.615 * VCCI (FF)
3.3 V PCI-X	0.285 * VCCI (RR)
	0.615 * VCCI (FF)

Table 2-23 • **Summary of I/O Timing Characteristics—Software Default Settings**
–1 Speed Grade, Automotive-Case Conditions: T_J = 115°C, Worst Case VCC = 1.425 V
Worst Case VCCI = 3.0 V
Standard Plus I/O Banks

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.55	3.36	0.04	0.97	0.39	3.42	1.56	3.05	1.94	5.55	2.80	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.05	0.04	1.23	0.39	3.11	2.99	1.56	1.69	5.23	5.11	ns
1.8 V LVCMOS	8 mA	High	35 pF	–	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.99	ns
1.5 V LVCMOS	4 mA	High	35 pF	–	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.18	ns
3.3 V PCI	Per PCI spec	High	10 pF	25 [2]	0.55	2.55	0.04	0.82	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25 [2]	0.55	2.55	0.04	0.79	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*
2. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-48 for connectivity. This resistor is not required during normal operation.*

Output Register

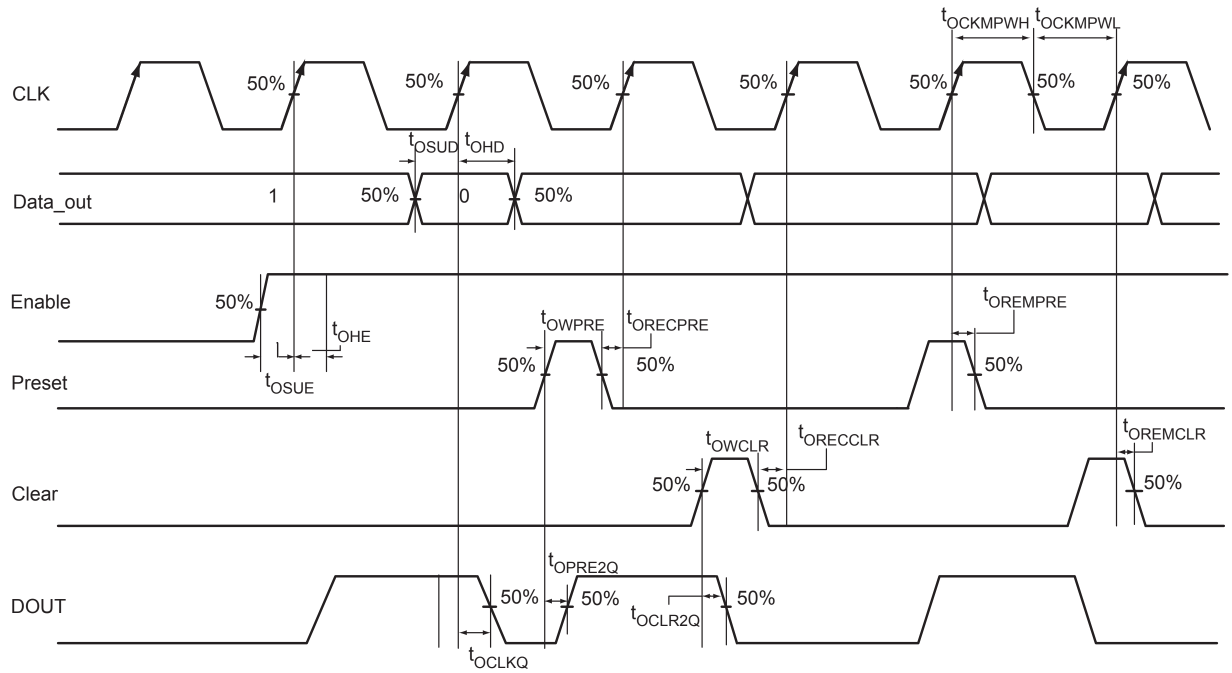

Figure 2-18 • **Output Register Timing Diagram**

Timing Characteristics

Table 2-94 • **Output Data Register Propagation Delays**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.72	0.84	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.38	0.45	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.53	0.63	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.98	1.15	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.98	1.15	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.27	0.32	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.27	0.32	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to *Table 2-5 on page 2-5* *for derating values.*

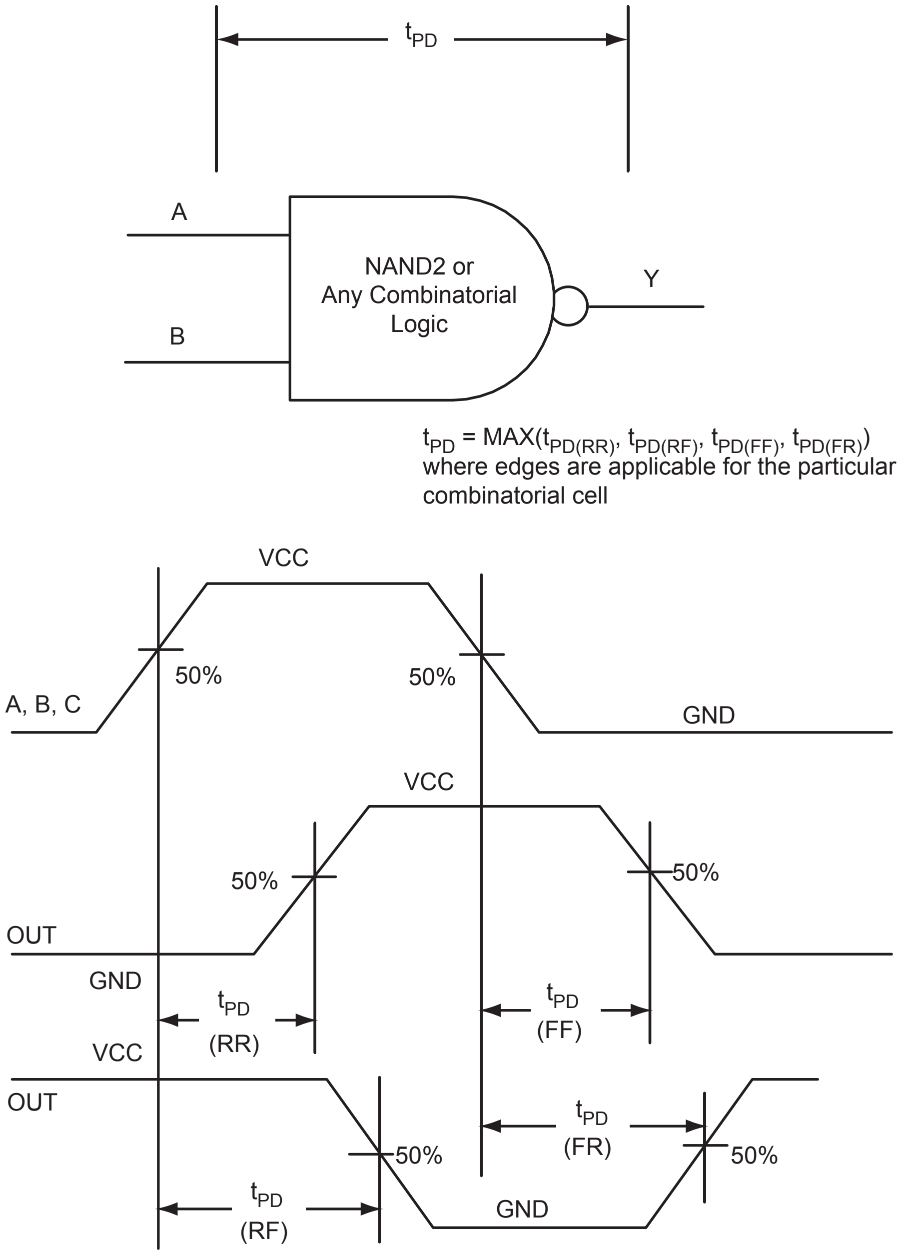

***Figure 2-25* • Timing Model and Waveforms**

Table 2-107 **• Register Delays**
Automotive-Case Conditions: T_J = 115°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.66	0.77	ns
t_{SUD}	Data Setup Time for the Core Register	0.51	0.60	ns
t_{HD}	Data Hold Time for the Core Register	0.00	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.54	0.64	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.48	0.56	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.48	0.56	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.27	0.31	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.27	0.31	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.25	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.25	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.41	0.48	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-118 **• RAM512X18**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{AS}	Address Setup Time	0.30	0.35	ns
t_{AH}	Address Hold Time	0.00	0.00	ns
t_{ENS}	REN, WEN Setup Time	0.11	0.13	ns
t_{ENH}	REN, WEN Hold Time	0.07	0.08	ns
t_{DS}	Input data (WD) Setup Time	0.22	0.26	ns
t_{DH}	Input data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (output retained)	2.58	3.03	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.07	1.26	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.43	0.50	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.50	0.59	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.10	1.29	ns
	RESET Low to Data Out Low on RD (pipelined)	1.10	1.29	ns
$t_{REMRSTB}$	RESET Removal	0.34	0.40	ns
$t_{RECRSTB}$	RESET Recovery	1.79	2.10	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.25	0.30	ns
t_{CYC}	Clock Cycle Time	3.85	4.53	ns
F_{MAX}	Maximum Frequency	255	217	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to* *Table 2-5 on page 2-5* *for derating values.*

FIFO

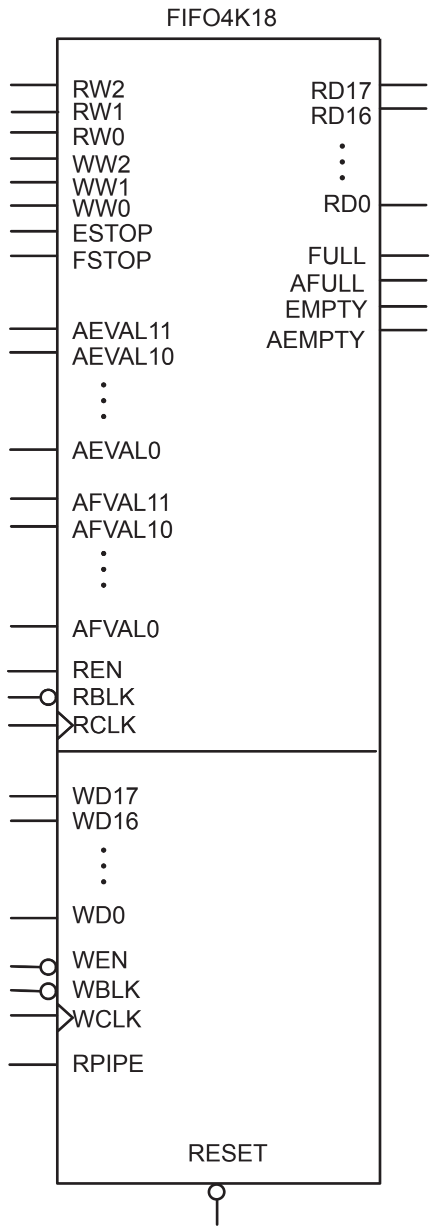

Figure 2-36 • **FIFO Model**

Timing Characteristics

Table 2-121 • FIFO
Worst-Case Automotive Conditions: T_J = 135°C, VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.97	1.67	ns
t_{ENH}	REN, WEN Hold Time	0.03	0.02	ns
t_{BKS}	BLK Setup Time	0.28	0.32	ns
t_{BKH}	BLK Hold Time	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.26	0.22	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.37	2.86	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.28	1.09	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.45	2.09	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.33	1.98	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	8.85	7.53	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.42	2.06	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	8.76	7.45	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.32	1.12	ns
	RESET Low to Data Out Low on RD (pipelined)	1.32	1.12	ns
$t_{REMRSTB}$	RESET Removal	0.41	0.35	ns
$t_{RECRSTB}$	RESET Recovery	2.14	1.82	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.30	0.26	ns
t_{CYC}	Clock Cycle Time	4.62	3.93	ns
F_{MAX}	Maximum Frequency for FIFO	217	255	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-12 for more details.

Timing Characteristics

***Table 2-125* • JTAG 1532**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{DISU}	Test Data Input Setup Time				ns
t_{DIHD}	Test Data Input Hold Time				ns
t_{TMSSU}	Test Mode Select Setup Time				ns
t_{TMDHD}	Test Mode Select Hold Time				ns
t_{TCK2Q}	Clock to Q (data out)				ns
t_{RSTB2Q}	Reset to Q (data out)				ns
F_{TCKMAX}	TCK Maximum Frequency	20	20	20	MHz
$t_{TRSTREM}$	ResetB Removal Time				ns
$t_{TRSTREC}$	ResetB Recovery Time				ns
$t_{TRSTMPW}$	ResetB Minimum Pulse				ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

VQ100	
Pin Number	**A3P125 Function**
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

QN132	
Pin Number	A3P125 Function
C17	IO83RSB1
C18	VCCIB1
C19	TCK
C20	VMV1
C21	VPUMP
C22	VJTAG
C23	VCCIB0
C24	NC
C25	NC
C26	GCA1/IO55RSB0
C27	GCC0/IO52RSB0
C28	VCCIB0
C29	IO42RSB0
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG256	
Pin Number	A3P1000 Function
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2

FG256	
Pin Number	A3P1000 Function
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the Automotive ProASIC3 datasheet.

Revision	Changes	Page
Revision 5 (January 2013)	The "Automotive ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43222).	1-III
	Added a note to Table 2-2 • Recommended Operating Conditions (SAR 43675): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in Table 2-116 • Automotive ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42560).	2-80
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 4 (September 2012)	The "Specifying I/O States During Programming" section is new (SAR 34691).	1-6
	Table 2-2 • Recommended Operating Conditions was revised to change VPUMP values for programming mode from "3.0 to 3.6" to "3.15 to 3.45" (SAR 34703).	2-2
	Maximum values for VIL and VIH were corrected in LVPECL Table 2-86 • Minimum and Maximum DC Input and Output Levels (SAR 37693).	2-52
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in the following tables (SAR 34804): Table 2-99 • Input DDR Propagation Delays (T_J = 135°C) Table 2-100 • Input DDR Propagation Delays (T_J = 115°C) Table 2-102 • Output DDR Propagation Delays (T_J = 135°C) Table 2-103 • Output DDR Propagation Delays (T_J = 115°C)	2-64 to 2-68
	Added values for minimum pulse width and removed the FRMAX row from Table 2-108 through Table 2-115 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 36966).	2-76
	SRAM collision data was added to Table 2-117 • RAM4K9 through Table 2-120 • RAM512X18. Maximum frequency, F_{MAX}, was updated in Table 2-118 • RAM512X18 (SAR 40859).	2-86 to 2-89
	The "VMVx I/O Supply Voltage (quiet)" section was revised. The sentence, "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" was replaced with, "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38323). VMV pins must be connected to the corresponding VCCI pins, as noted in the "VMVx I/O Supply Voltage (quiet)" section, for an ESD enhancement.	3-1
	Libero Integrated Design Environment (IDE) was changed to Libero Systeom-on-Chip (SoC) throughout the document (SAR 40266).	N/A
Revision 3 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1

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